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20 V, 5 A P-channel Trench MOSFET Rev. 1 — 9 May 2011

Product data sheet

Product profile 1.

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 1.8 V R_{DSon} rated
- Very fast switching

1.3 Applications

- Relay driver
- High-speed line driver

- Trench MOSFET technology
- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; \text{ T}_{amb} = 25 \text{ °C}$	[1]	-	-	-5	А
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I _D = -2.4 A; T _j = 25 °C		-	34	40	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Pinning information 2.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain		5
2	D	drain		
3	G	gate	0	
4	S	source		
5	D	drain	SOT457 (TSOP6)	Ś
6	D	drain		017aaa094



3. Ordering information

Table 3.Ordering information			
Type number	Package		
	Name	Description	Version
PMN34UP	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457

4. Marking

Table 4.Marking codes

Type number	Marking code
PMN34UP	ZY

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	$T_j = 25 \ ^{\circ}C$		-	-20	V
V _{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; \text{ T}_{amb} = 25 \text{ °C}$	<u>[1]</u>	-	-5	А
		$V_{GS} = -4.5 \text{ V}; \text{ T}_{amb} = 100 \text{ °C}$	<u>[1]</u>	-	-3.1	А
I _{DM}	peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \mu\text{s}$		-	-20	А
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	540	mW
			<u>[1]</u>	-	1385	mW
		T _{sp} = 25 °C		-	6250	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode					
I _S	source current	T _{amb} = 25 °C	[1]	-	-1.5	А

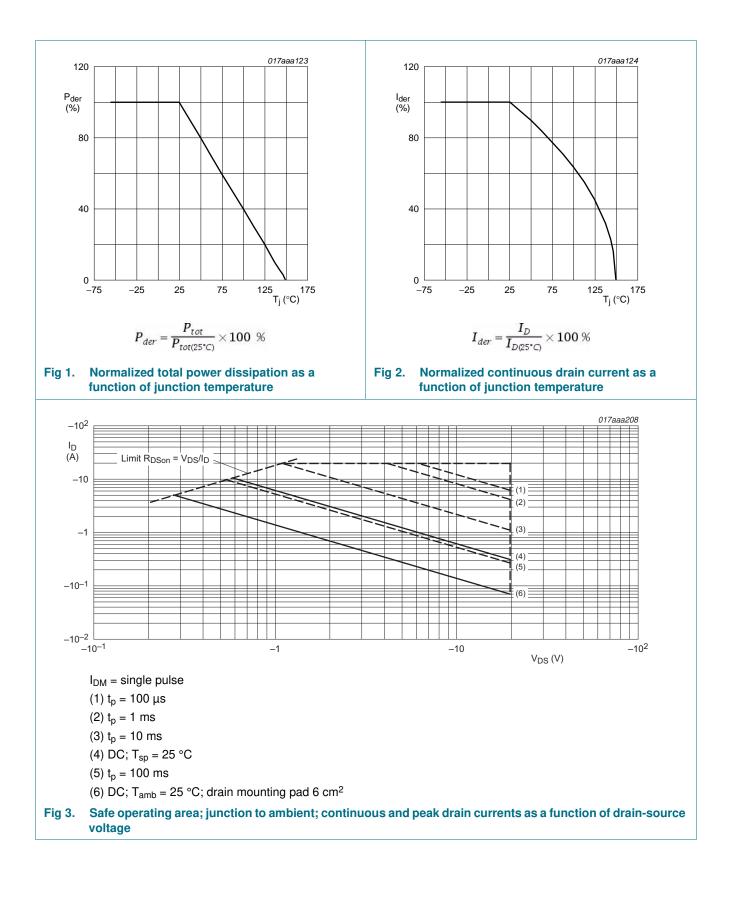
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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Product data sheet

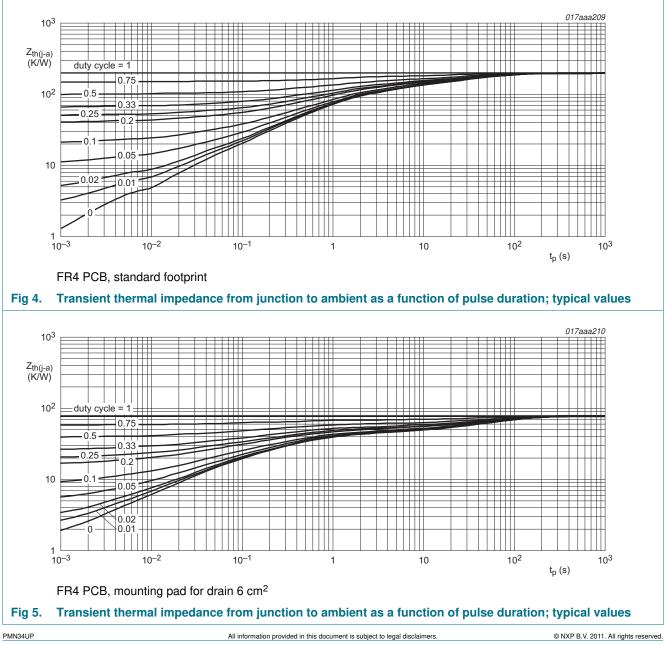
20 V, 5 A P-channel Trench MOSFET

6. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	<u>[1]</u>	-	200	230	K/W
	from junction to ambient		[2]	-	78	90	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	15	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

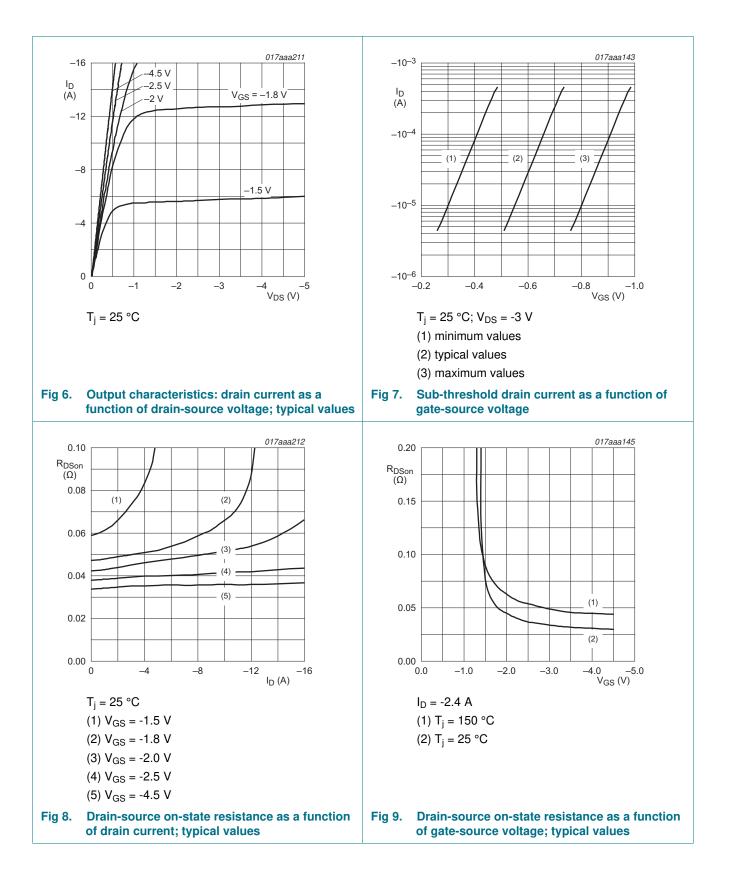


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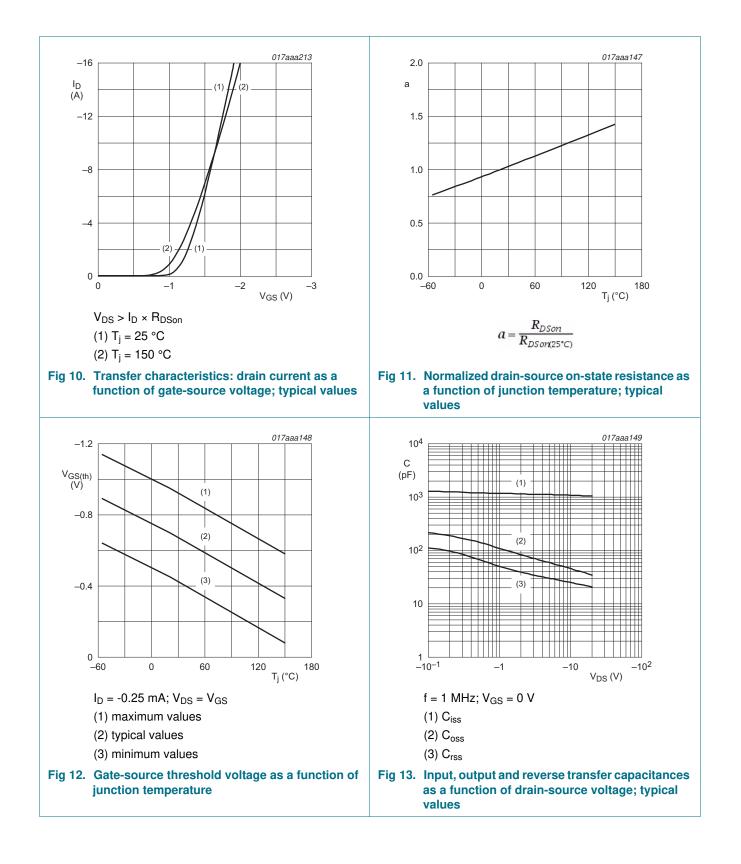
7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = -250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	-20	-	-	V
V _{GSth}	gate-source threshold voltage	$I_D = -250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^\circ\text{C}$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μA
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μA
I _{GSS}	gate leakage current	$V_{GS} = -8 V; V_{DS} = 0 V; T_j = 25 \text{ °C}$	-	-	-100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I _D = -2.4 A; T _j = 25 °C	-	34	40	mΩ
		V_{GS} = -4.5 V; I _D = -2.4 A; T _j = 150 °C	-	48	55	mΩ
		V_{GS} = -2.5 V; I _D = -2.0 A; T _j = 25 °C	-	42	48	mΩ
		V_{GS} = -1.8 V; I _D = -1.8 A; T _j = 25 °C	-	57	66	mΩ
9 _{fs}	forward transconductance	V_{DS} = -5 V; I _D = -2.4 A; T _j = 25 °C	-	13	-	S
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_D = -1 A; V_{GS} = -4.5 V;	-	15.5	23	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}$	-	2.5	-	nC
Q _{GD}	gate-drain charge		-	2	-	nC
C _{iss}	input capacitance	V_{DS} = -10 V; f = 1 MHz; V_{GS} = 0 V;	-	1950	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	175	-	pF
C _{rss}	reverse transfer capacitance		-	105	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = -10 \ V; \ V_{GS} = -5 \ V; \ R_{G(ext)} = 6 \ \Omega;$	-	13	-	ns
t _r	rise time	$T_j = 25 \text{ °C}; I_D = -1 \text{ A}$	-	21	-	ns
t _{d(off)}	turn-off delay time		-	95	-	ns
t _f	fall time		-	33	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	I _S = -2.4 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.75	-1	V

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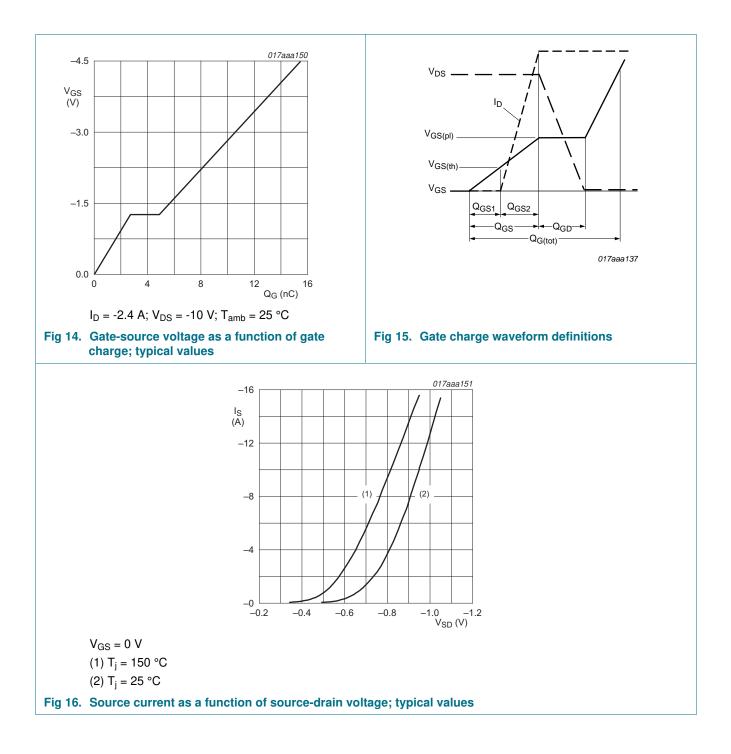
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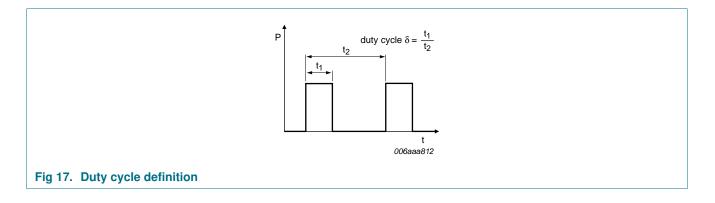
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8. Test information



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9. Package outline

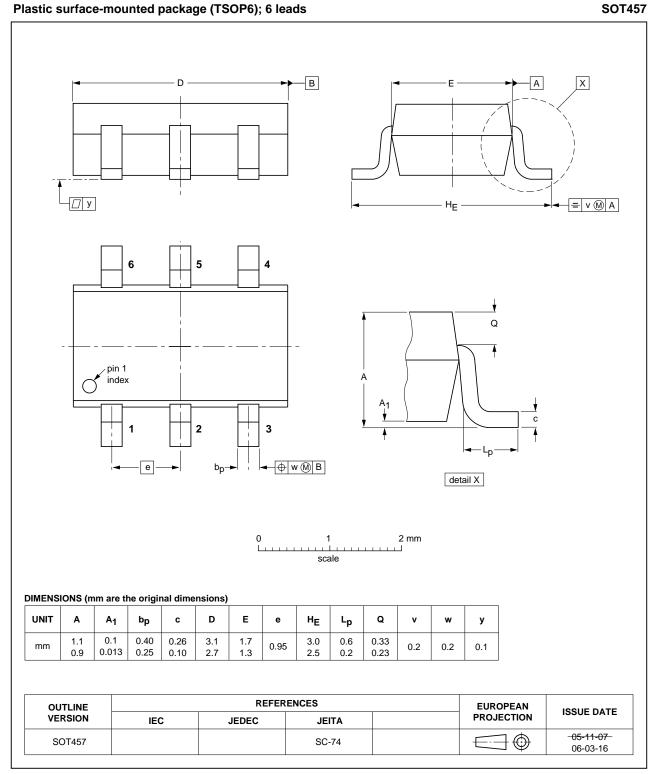
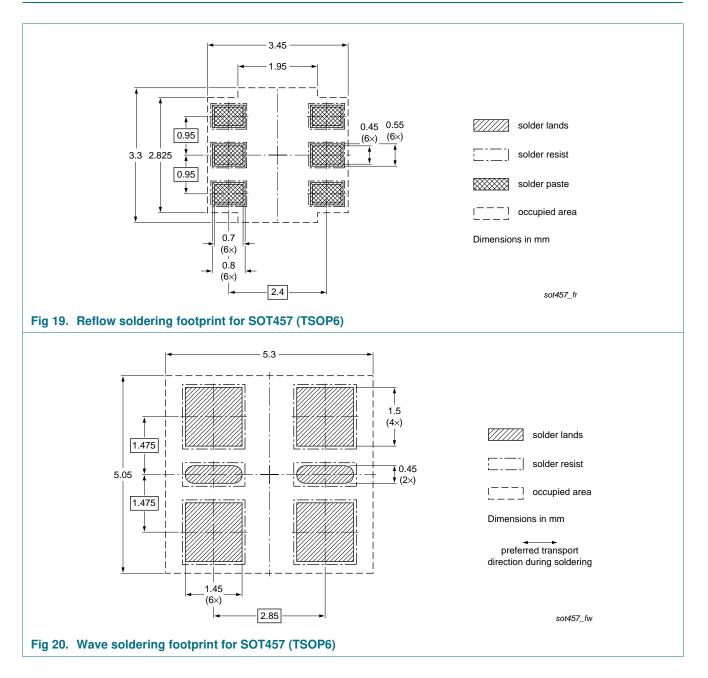


Fig 18. Package outline SOT457 (TSOP6)

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10. Soldering



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11. Revision history

Table 8. F	Revision history						
Document I	D Release date	Data sheet status	Change notice	Supersedes			
PMN34UP v	.1 20110509	Product data sheet	-	-			

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12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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